

ABSTRACT OF THE DISCLOSURE

ETCHING METHOD

5 An etching method for etching a silicon
oxide film is provided that includes generating a
plasma from a gas including a hydrogen-containing
gas and a fluorine-containing gas using a high
frequency power for plasma generation, and etching
10 the silicon oxide film using the generated plasma.
The fluorine-containing gas includes a
hydrofluorocarbon gas, and the sticking coefficient
of radicals generated from the hydrofluorocarbon gas
is higher than the sticking coefficient of radicals
15 generated from carbon tetrafluoride (CF_4).

FIG. 8A-8D